

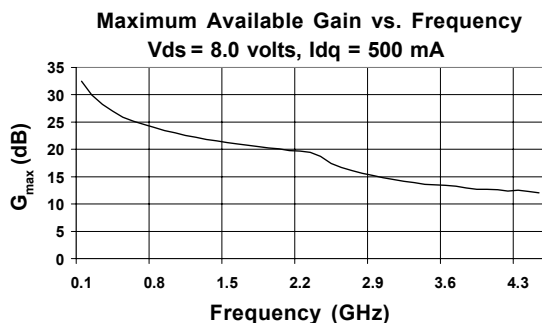


Product Description

Stanford Microdevices' SHF-0589 series is a high performance GaAs Heterostructure FET housed in a low-cost surface-mount plastic package. HFET technology improves breakdown voltage while minimizing Schottky leakage current for higher power added efficiency and improved linearity.

Output power at 1dB compression for the SHF-0589 is +34dBm when biased for Class AB operation at 8V and 500mA. The +45 dBm third order intercept makes it ideal for high dynamic range, high intercept point requirements. They are well suited for use in both analog and digital wireless communication infrastructure and subscriber equipment including cellular PCS, CDPD, wireless data, and pagers.

Adequate heat sinking must be provided for this part to avoid exceeding the maximum junction temperature. Methods include the use of screws near the device, and filled vias beneath the part to the ground plane. Refer to "Mounting and Thermal Considerations" section on page 7 for more information.



Electrical Specifications at Ta = 25°C

Symbol	Parameters: Test Conditions		Units	Min.	Typ.	Max.
$ S_{21} ^2$	Insertion Power Gain Vds = 8.0V, Idq = 500 mA, Z _S =Z _L =50 Ohms	f = 0.9 GHz f = 1.9 GHz	dB		15.6 9.4	
G _{max}	Maximum Available Gain Vds = 8.0V, Idq = 500 mA, Z _S =Z _{S OPT} , Z _L =Z _{L OPT}	f = 0.9 GHz f = 1.9 GHz	dB		24 20	
TOIP	Output Third Order Intercept Point (Device is tuned for maximum power output)	f = 0.9 GHz f = 1.9 GHz	dBm dBm		46 45	
I _{DSS}	Saturated Drain Current Vds = 3.0V, Vgs = 0V		mA		1176	
G _m	Transconductance: Vds = 3.0V, Vgs = 0V		mS		792	
V _p	Pinch-Off Voltage: Vds = 2.0V, Id = 2.4 mA		V	-2.7	-1.9	-1.0
V _{bgs}	Gate-to-Source Breakdown Voltage, Igs = 4.8mA		V		-22	-17
V _{bgd}	Gate-to-Drain Breakdown Voltage, Igd = 4.8mA		V		-22	-17
R _{th}	Thermal Resistance, junction-to-lead		°C/W		21	

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Preliminary

SHF-0589

DC-3 GHz, 2.0 Watt GaAs HFET



Product Features

- Patented GaAs Heterostructure FET Technology
- +34 dBm Output Power at 1 dB Compression
- +45 dBm Output IP3
- High Drain Efficiency: Up to 50% at Class AB
- 15 dB Gain at 900 MHz (Application circuit)
- 11 dB Gain at 1900 MHz (Application circuit)

Applications

- Analog and Digital Wireless System
- Cellular PCS, CDPD, Wireless Data, Pagers

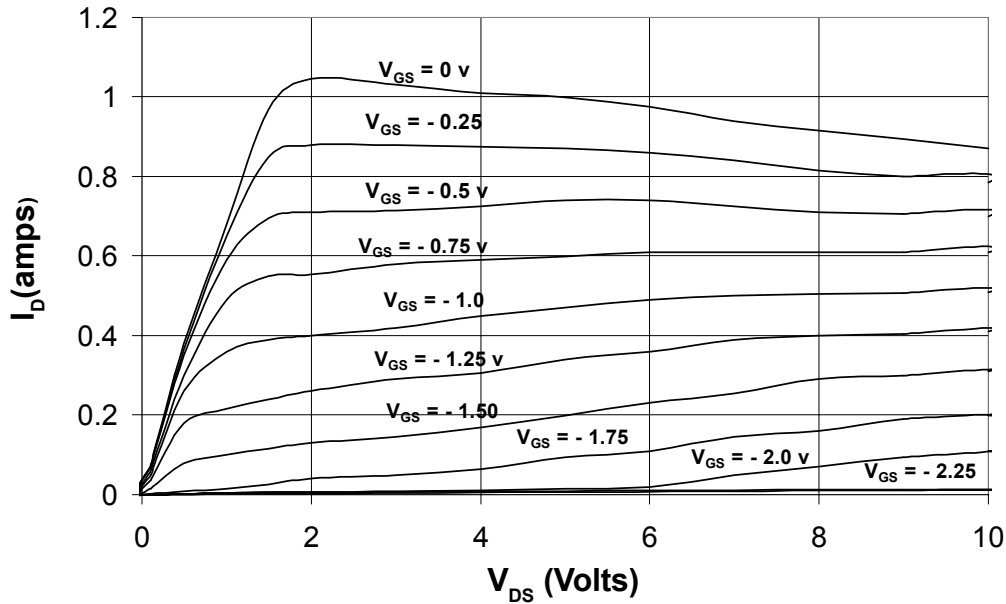
Absolute Maximum Ratings

Notes:

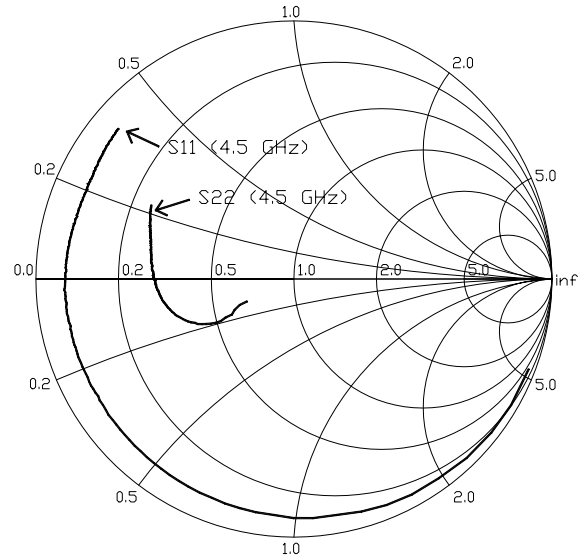
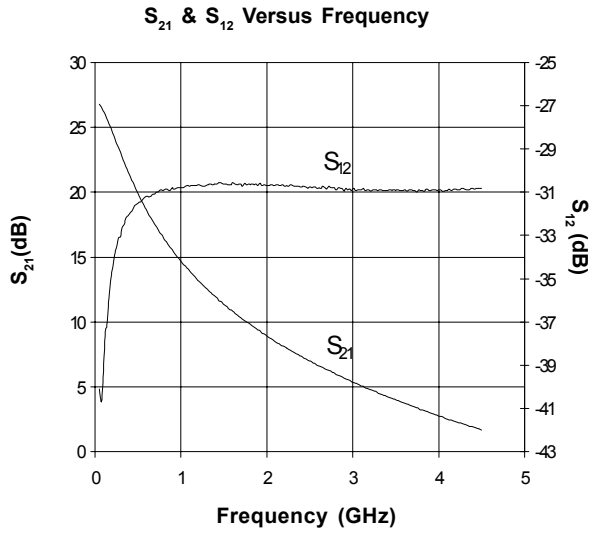
1. Operation of this device above any one of these parameters may cause permanent damage.

Parameter	Symbol	Absolute Maximum
Drain-to-Source Voltage	V_{DS}	+12V
Gate-to-Source Voltage	V_{GS}	-5V to 0V
Drain Current	I_{DS}	IDSS
Operating Temperature	T_{OP}	-45 C to +85° C
RF Input Power	P_N	500 mW
Channel Temperature	T_{CH}	+175° C
Storage Temperature	T_{STG}	-65 to +150° C

Plot of I_D vs. V_{DS} for $V_{GS} = -2.25V$ to $0V$



NOTE: I/V curves were taken using pulse sampling techniques. This results in low duty cycle currents through the device and therefore very low power levels. It is not recommended that these measurements be taken in d.c. mode, as excessive current could result in damage to the device.



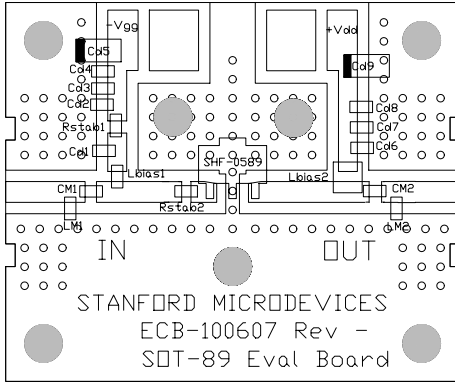
S11 & S22 vs. Frequency (0.1 to 4.5 GHz)

Typical s-parameters at 25° C (Vds = 8V, Ids = 500mA)

Freq(GHz)	S11	S11 Ang	S21 dB	S21	S21 Ang	S12 dB	S12	S12 Ang	S22	S22 Ang
0.05	0.98	-21.9	26.8	21.9	165.2	-40.1	0.01	86.9	0.19	-149.3
0.1	0.97	-40.0	26.3	20.6	155.9	-39.8	0.01	66.1	0.25	-148.2
0.3	0.92	-98.2	23.0	14.2	125.0	-33.1	0.02	38.5	0.41	-155.7
0.5	0.90	-127.9	20.0	10.0	108.1	-31.5	0.03	24.1	0.47	-164.2
0.7	0.89	-144.5	17.5	7.5	97.5	-31.1	0.03	16.8	0.50	-169.5
0.9	0.89	-155.5	15.6	6.0	89.6	-30.8	0.03	11.5	0.51	-173.2
1.1	0.89	-163.4	13.9	5.0	82.9	-30.7	0.03	7.8	0.52	-176.0
1.3	0.89	-169.5	12.6	4.2	77.4	-30.7	0.03	5.1	0.52	-178.5
1.5	0.89	-174.9	11.4	3.7	71.8	-30.6	0.03	2.8	0.53	179.3
1.7	0.89	179.2	10.3	3.3	66.7	-30.6	0.03	0.8	0.53	177.6
1.9	0.88	176.5	9.4	2.9	62.2	-30.7	0.03	-1.6	0.54	175.6
2.1	0.89	172.9	8.5	2.7	57.5	-30.7	0.03	-2.7	0.54	174.2
2.3	0.88	169.5	7.7	2.4	53.2	-30.7	0.03	-4.1	0.55	172.1
2.5	0.88	166.3	7.0	2.2	49.0	-30.7	0.03	-5.4	0.55	170.5
3.0	0.87	158.5	5.3	1.8	38.4	-30.8	0.03	-7.8	0.56	166.3
3.5	0.88	151.3	4.0	1.6	28.6	-30.9	0.03	-9.2	0.58	162.3
4.0	0.89	144.4	2.7	1.4	19.2	-30.9	0.03	-10.0	0.60	158.1
4.5	0.90	138.6	1.7	1.2	10.1	-30.8	0.03	-11.0	0.61	153.7

No external matching, Scattering parameters are de-embedded on test fixture to device lead at package edge.

900 MHz Application Circuit at 25° C (Vds=8V, Idq=500mA)



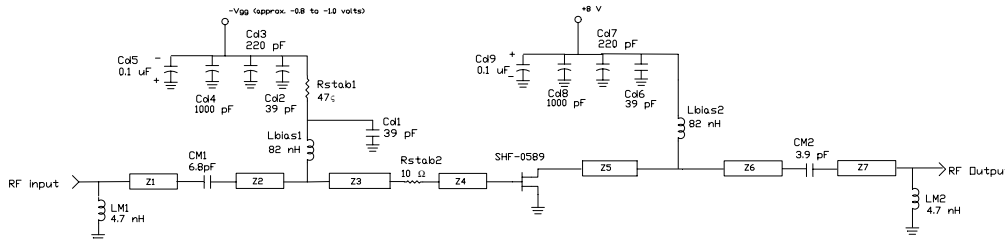
Ref. desig.	Value	Part Number /Style
Cd1,2,6	39 pF	ROHM MCH18 series
Cd3,7	220 pF	ROHM MCH18 series
Cd4,8	1000 pF	ROHM MCH18 series
Cd5,9	0.1 uF	TANTALUM, size"A", 35 volt
CM1	6.8 pF	ROHM MCH18 series
CM2	3.9 pF	ROHM MCH18 series
LM1,2	4.7 nH	TOKO LL1005-FH4N7K
Lbias1	82 nH	TOKO LL1608-FH82NT
Lbias2	82 nH	COILCRAFT 1008CS-820XJB
Rstab1	47 ohms	size 0603
Rstab2	10 ohms	size 0603

Microstrip Segment Specifications

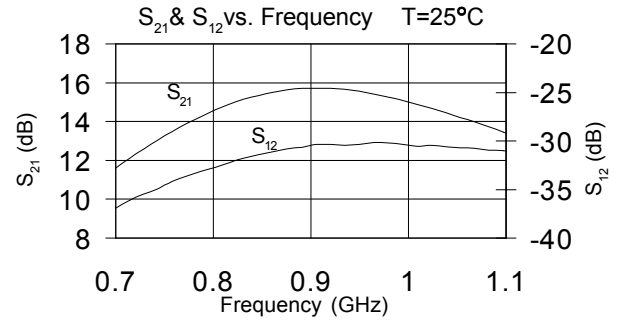
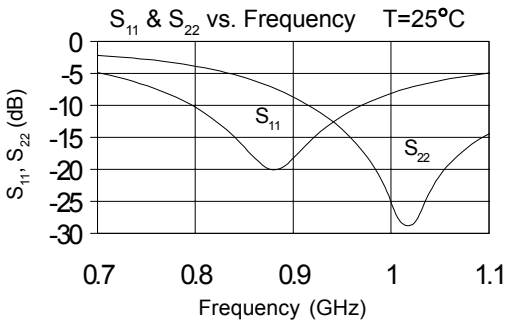
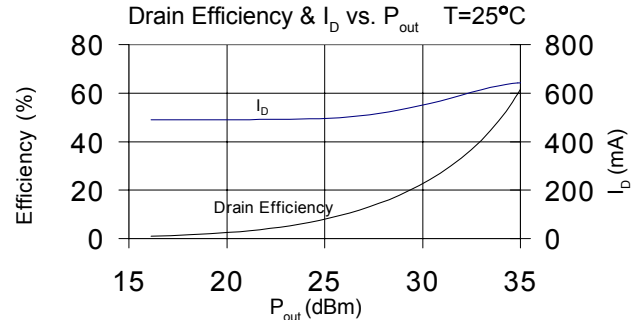
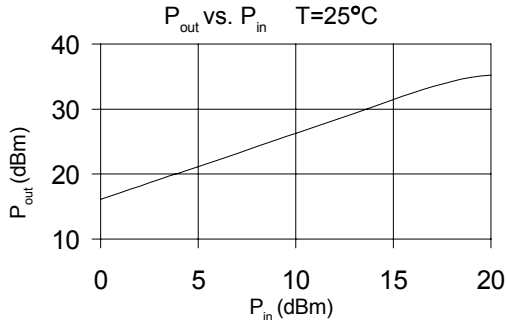
Ref. desig.	Value
Z1	50 ohms, 2.6 deg. @ 900 MHz
Z2	50 ohms, 3.5 deg. @ 900 MHz
Z3	50 ohms, 8.8 deg. @ 900 MHz
Z4	50 ohms, 3.1 deg. @ 900 MHz
Z5	50 ohms, 11.7 deg. @ 900 MHz
Z6	50 ohms, 3.6 deg. @ 900 MHz
Z7	50 ohms, 2.6 deg. @ 900 MHz

Phase shift functional block between components are calculated based on wavelength of 900 MHz signal on FR4 board material with dielectric constant of 4.1, microstrip width and height dimensions of W=.054 inch and h=.031 inch.

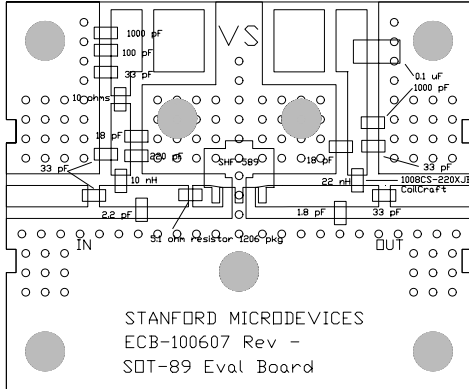
Test Data @ 0.9 GHz
 P_{1dB} (dBm) $IP3$ (dBm) Output tone Level (dBm)
 34.4 45.8 15



Stanford Microdevices 2-18-2000
 SHF-0589 900 MHz Application Circuit



1.9 GHz Application Circuit at 25°C (Vds=8V, Idq=500mA)



Ref. desig.	Value	Part Number /Style
Cd1,6,8	33 pF	ROHM MCH18 series
Cd2	220 pF	ROHM MCH18 series
Cd3,7	18 pF	ROHM MCH18 series
Cd4,9	1000 pF	ROHM MCH18 series
Cd5	100 pF	ROHM MCH18 series
Cd10	0.1 uF	Tantalum, size "A", 35V
CC1,2	33 pF	ROHM MCH18 series
CM1	2.2 pF	ROHM MCH18 series
CM2	1.8 pF	ROHM MCH18 series
Lbias1	10 nH	TOKO LL1608-FH10NT
Lbias2	22 nH	COILCRAFT 1008CS-220XJB
Rstab1	10 ohms	size 0603
Rstab2	5.1 ohms	size 0603

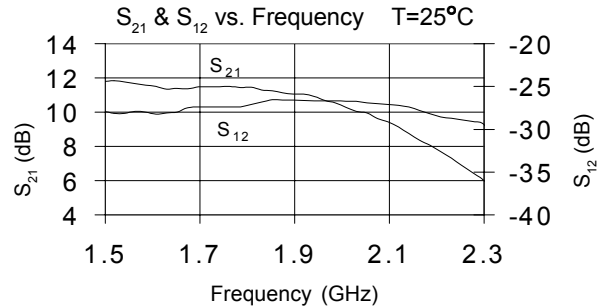
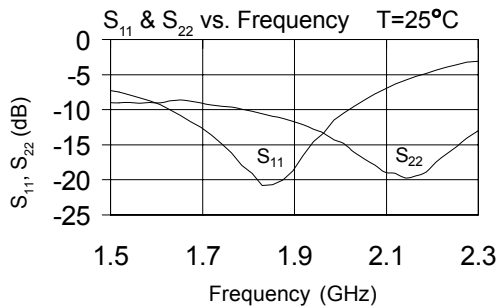
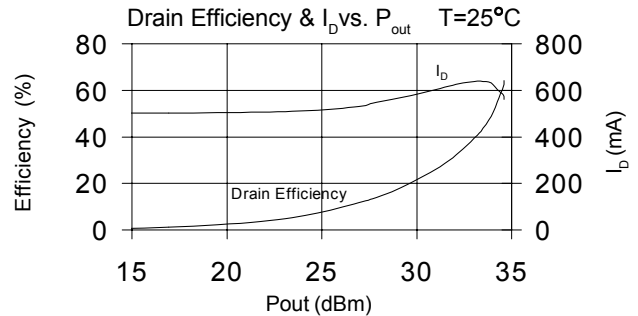
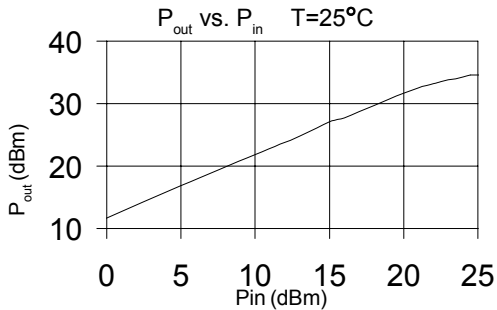
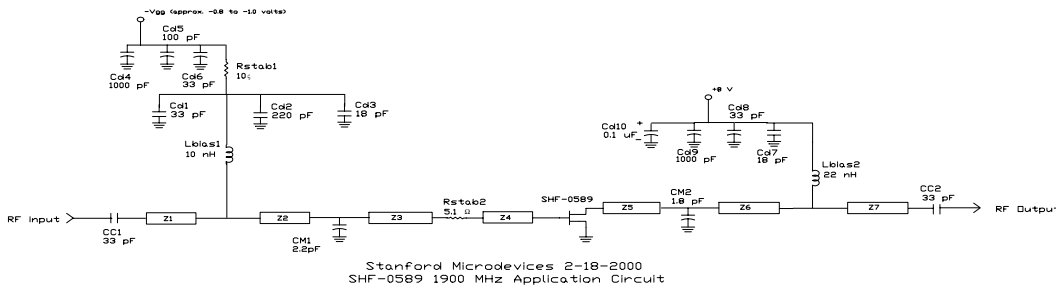
Microstrip Segment Specifications

Ref. desig.	Value
Z1	50 ohms, 7.3 deg. @ 1900 MHz
Z2	50 ohms, 5.3 deg. @ 1900 MHz
Z3	50 ohms, 12.9 deg. @ 1900 MHz
Z4	50 ohms, 6.6 deg. @ 1900 MHz
Z5	50 ohms, 20.6 deg. @ 1900 MHz
Z6	50 ohms, 4.5 deg. @ 1900 MHz
Z7	50 ohms, 7.1 deg. @ 1900 MHz

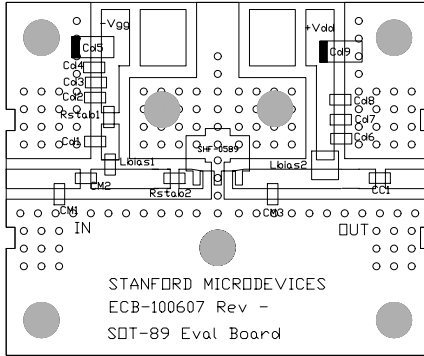
Phase shift functional block between components are calculated based on wavelength of 900 MHz signal on FR4 board material with dielectric constant of 4.1, microstrip width and height dimensions of W=.054 inch and h=.031 inch.

Test Data @ 1.9 GHz

P_{1dB} (dBm)	IP3 (dBm)	PAE	Eff (8V, 500mA)
34	45.6	46.2%	50.7%



2.45 GHz Application Circuit at 25°C (Vds=8V, Idq=500mA)



Ref. desig.	Value	Part Number /Style
Cd1,2,6	5.6 pF	ROHM MCH18 series
Cd3,7	68 pF	ROHM MCH18 series
Cd4,8	1000 pF	ROHM MCH18 series
Cd5,9	0.1 uF	Tantalum, size "A", 35V
CC1	5.6 pF	ROHM MCH18 series
CM1,3	1.8 pF	ROHM MCH18 series
CM2	1.2 pF	ROHM MCH18 series
Lbias1	15 nH	TOKO LL1608-FH15NT
Lbias2	18 nH	COILCRAFT 1008CS-180XJB
Rstab1	20 ohms	size 0603
Rstab2	2.2 ohms	size 0603

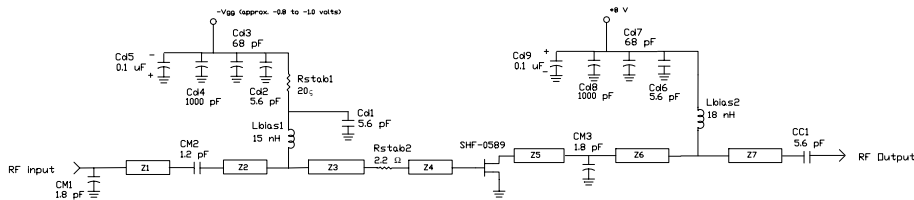
Microstrip Segment Specifications

Ref. desig.	Value
Z1	50 ohms, 9.7 deg. @ 2450 MHz
Z2	50 ohms, 9.3 deg. @ 2450 MHz
Z3	50 ohms, 24.2 deg. @ 2450 MHz
Z4	50 ohms, 8.0 deg. @ 2450 MHz
Z5	50 ohms, 12.7 deg. @ 2450 MHz
Z6	50 ohms, 19.4 deg. @ 2450 MHz
Z7	50 ohms, 20.4 deg. @ 2450 MHz

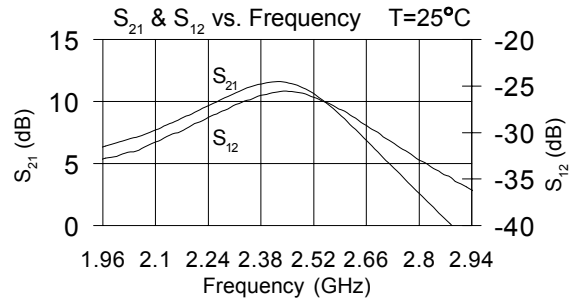
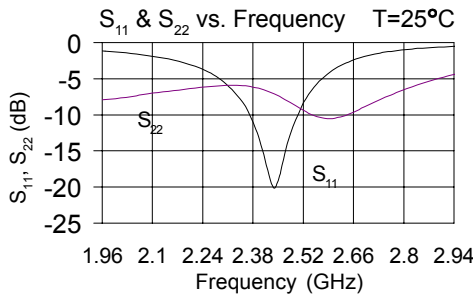
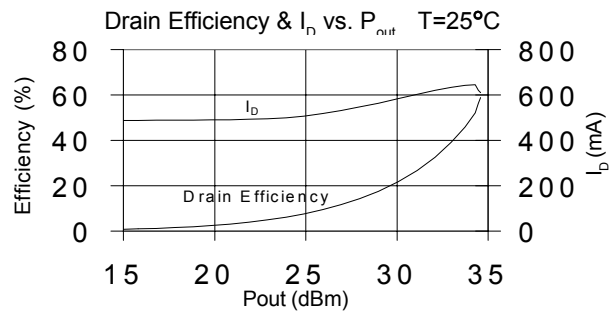
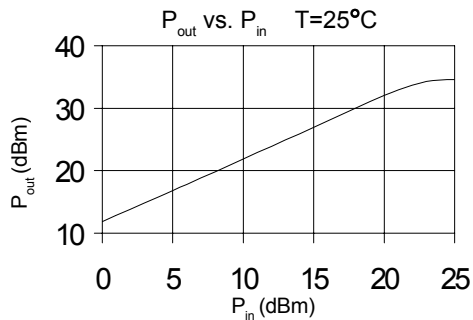
Phase shift functional block between components are calculated based on wavelength of 900 MHz signal on FR4 board material with dielectric constant of 4.1, microstrip width and height dimensions of W=.054 inch and h=.031 inch.

Test Data @ 2.45 Ghz

P_{1dB} (dBm)	IP3 (dBm)	Output tone Level (dBm)
34.7	44.26	15



Stanford Microdevices 2-18-2000
 SHF-0589 2450 MHz Application Circuit





Preliminary

SHF-0589 DC-3GHz, 2 Watt GaAs HFET



Caution: ESD sensitive
Appropriate precautions in handling, packaging and testing devices must be observed.

Part Number Ordering Information

Part Number	Devices Per Reel	Reel Size
SHF-0589	1000	7"

Mounting and Thermal Considerations:

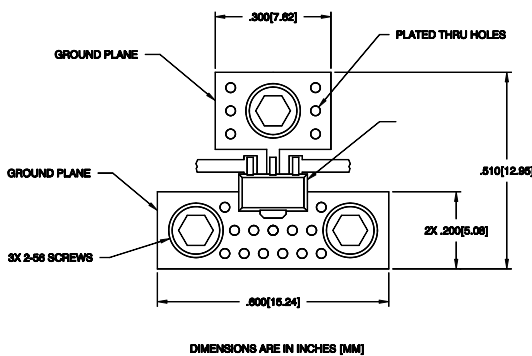
It is very important that adequate heat sinking be provided to avoid exceeding the maximum device junction temperature. All of the following suggestions should be followed to ensure maximum operating life of the device:

1. Use 2 ounce copper if possible.
2. Use a large ground pad area with many plated through-holes (solder filling is recommended).
3. Multiple filled vias are required directly below the SOT-89 ground tab.
4. Solder the copper pad on the backside of the device package to the ground plane.
5. Use three point board seating with 2-56 machine screws (no more than 0.2 inch from the device) to provide a low thermal resistance path to the mounting plate.
6. We recommend thermal transfer paste be used between the board and the mounting plate.

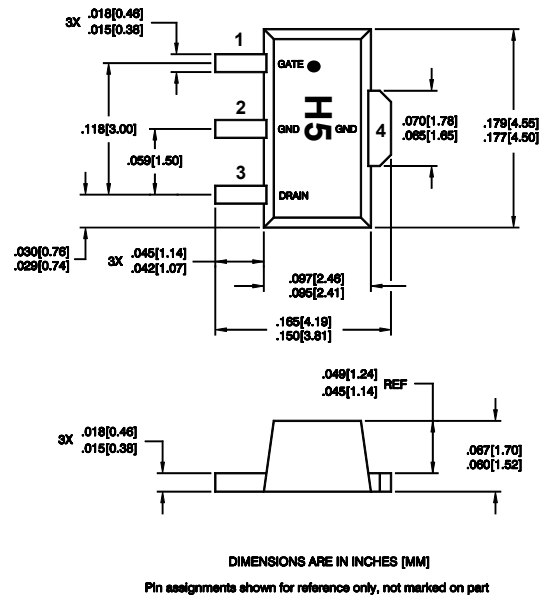
Part Symbolization

The part will be symbolized with a "H5" designator on the top surface of the package.

Pin Designation	
1	Gate
2	Source
3	Drain
4	Source



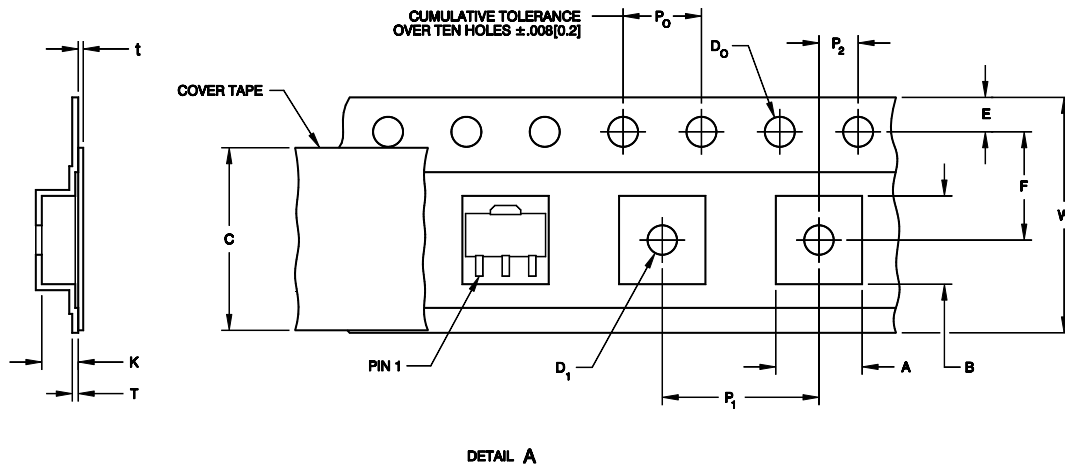
Outline Drawing



Component Tape and Reel Packaging

Tape Dimensions

For 89 Outline



Description		Symbol	Size (mm)
Cavity	Length	A	4.91 +/- 0.01
	Width	B	4.52 +/- 0.01
	Depth	K	1.90 +/- 0.01
	Pitch	P_1	8.00 +/- 0.01
	Bottom Hole Diameter	D_1	1.60 +/- 0.10
Perforation	Diameter	D_0	1.55 +/- 0.05
	Pitch	P_0	4.00 +/- 0.01
	Position	E	1.75 +/- 0.01
Cover Tape	Width	C	9.10 +/- 0.25
	Tape Thickness	t	0.05 +/- 0.01
Carrier Tape	Width	W	12.0 +/- 0.03
	Thickness	T	0.30 +/- 0.05
Distance	Cavity to Perforation (Width Direction)	F	5.50 +/- 0.10
	Cavity to Perforation (Length Direction)	P_2	2.00 +/- 0.10

Note: Drawing not to scale